Mustapha Diani

List of Publications by Year in descending order

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840776 794594 52 499 11 19 citations h-index g-index papers 52 52 52 314 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Search for carbon nitride CNx compounds with a high nitrogen content by electron cyclotron resonance plasma deposition. Diamond and Related Materials, 1994, 3, 264-269.	3.9	67
2	The Ge Stranski-Krastanov growth mode on Si(001) (2 \tilde{A} — 1) tested by X-ray photoelectron and Auger electron diffraction. Surface Science, 1993, 291, 110-116.	1.9	32
3	A particular epitaxial Si1 \hat{a} yCy alloy growth mode on Si(001) evidenced by cross-sectional transmission electron microscopy. Journal of Crystal Growth, 1995, 157, 420-425.	1.5	24
4	X-ray photoelectron diffraction observation of \hat{l}^2 -SiC(001) obtained by electron cyclotron resonance plasma assisted growth on Si(001). Applied Surface Science, 1993, 68, 575-582.	6.1	23
5	A First-Principles Investigation on Electronic Structure, Optical and Thermoelectric Properties of Janus In2SeTe Monolayer. Journal of Superconductivity and Novel Magnetism, 2021, 34, 3279-3290.	1.8	23
6	Strong element dependence of C 1s and Si 2p X-ray photoelectron diffraction profiles for identical C and Si local geometries in \hat{I}^2 -SiC. Surface Science, 1995, 339, 363-371.	1.9	20
7	Oxygen vacancies and defects tailored microstructural, optical and electrochemical properties of Gd doped CeO2 nanocrystalline thin films. Materials Science in Semiconductor Processing, 2022, 145, 106631.	4.0	20
8	Selective thermal â€" as opposed to non-selective plasma â€" nitridation of Siî—,Ge related materials examined by in situ photoemission techniques. Journal of Non-Crystalline Solids, 1995, 187, 319-323.	3.1	15
9	Electronic structure, optical and thermoelectric properties of Ge2SeS monolayer via first-principles study. Physica E: Low-Dimensional Systems and Nanostructures, 2022, 136, 115022.	2.7	15
10	Crystal growth of 3C–SiC polytype on 6H–SiC(0001) substrate. Journal of Crystal Growth, 2002, 235, 95-102.	1.5	13
11	An experimental characterization of $\mathrm{Si}(111)$ surfaces by $\mathrm{Si}\ 2p\ X$ -ray photoelectron diffraction. Solid State Communications, 1992, 83, 823-827.	1.9	12
12	Observation of Si out-diffusion related defects in SiC growth on Si(001). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 29, 110-113.	3.5	11
13	Synthesis of epitaxial Si1 â^ yCy alloys on Si(001) with high level of non-usual substitutional carbon incorporation. Journal of Crystal Growth, 1995, 157, 431-435.	1.5	10
14	Tailoring the germanene–substrate interactions by means of hydrogenation. Physical Chemistry Chemical Physics, 2016, 18, 15667-15672.	2.8	10
15	Performance evaluation and analysis of polycrystalline photovoltaic plant located in Northern Morocco. International Journal of Ambient Energy, 2022, 43, 1262-1268.	2.5	10
16	First-principles study on electronic and thermoelectric properties of Janus monolayers AsXC3 (X: Sb,) Tj ETQq0 (0 rgBT /C	verlock 10 Tf !
17	First-principles calculations to investigate structural, electronic and optical properties of Janus AsMC3 (M: Sb, Bi) monolayers for optoelectronic applications. Solid State Communications, 2022, 343, 114667.	1.9	10
18	Ge quantum dots on a large band gap semiconductor: the first growth stages on 4H–SiC(0001). Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 428-434.	2.7	9

#	Article	IF	CITATIONS
19	Synthesis, structural and optical characteristics of vanadium doped cerium dioxide layers. Materialia, 2021, 18, 101143.	2.7	9
20	Strain effects on the structural, electronic, optical and thermoelectric properties of <scp>Si₂SeS</scp> monolayer with puckered honeycomb structure: A firstâ€principles study. International Journal of Quantum Chemistry, 2022, 122, .	2.0	9
21	Xâ€ray photoelectron and Auger electron diffraction probing of Ge heteroepitaxy on Si (001) 2×1. Jour of Applied Physics, 1993, 73, 7412-7415.	nal 2.5	8
22	Influence of the surface-termination of hexagonal SiC(0001) on the temperature dependences of Ge growth modes and desorption. Surface Science, 2003, 546, 1-11.	1.9	8
23	6H- AND 4H-SiC(0001) SI SURFACE RICHNESS DOSING BY HYDROGEN ETCHING: A WAY TO REDUCE THE FORMATION TEMPERATURE OF RECONSTRUCTIONS. Surface Review and Letters, 2003, 10, 55-63.	1.1	8
24	Using strain to control molecule chemisorption on silicene. Journal of Chemical Physics, 2017, 147, 044705.	3.0	8
25	Undulated silicene and germanene freestanding layers: why not?. Journal of Physics Condensed Matter, 2020, 32, 195503.	1.8	7
26	Na adsorption on bismuthene monolayer for battery applications: A first-principles study. FlatChem, 2021, 27, 100251.	5.6	7
27	Effect of indium doping on the structural, optical and electrochemical behaviors of CeO2 nanocrystalline thin films. Optical Materials, 2022, 127, 112312.	3.6	7
28	Epitaxy relationships between Ge-islands and SiC(0001). Applied Surface Science, 2005, 241, 403-411.	6.1	6
29	Original Ge-induced phenomena on various SiC(0 0 01) reconstructions. Journal Physics D: Applied Physics, 2007, 40, 6225-6241.	2.8	6
30	Physical properties and electrochemical behavior of thin layers of vanadium doped cerium dioxide. Surfaces and Interfaces, 2021, 23, 100906.	3.0	6
31	Efficient planar heterojunction based on α-sexithiophene/fullerene through the use of MoO3/CuI anode buffer layer. Thin Solid Films, 2022, 741, 139025.	1.8	6
32	First-principles investigations of structural, electronic and thermoelectric properties of Sb/Bi2Se3 van der Waals heterostructure. Materials Science in Semiconductor Processing, 2022, 142, 106472.	4.0	6
33	First-principles prediction of stable Janus BiSbC3 monolayer with tunable electronic and optical properties under strain. Computational Condensed Matter, 2022, 31, e00687.	2.1	6
34	High thermoelectric figure of merit for GeS/phosphorene 2D heterostructures: A first-principles study. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2022, 281, 115737.	3. 5	6
35	Surface structure of Si(001) treated by hydrogen and argon electron cyclotron resonance plasmas. Applied Surface Science, 1992, 62, 67-75.	6.1	5
36	A structural parallel between Ge- and Si-induced $4\tilde{A}$ —4 and $3\tilde{A}$ —3 reconstructions on SiC(0001) drawn from comparative RHEED oscillations. Surface Science, 2004, 565, 57-69.	1.9	5

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37	In-situ surface technique analyses and ex-situ characterization of Si1-xGex epilayers grown on Si(001)-2 ×1 by molecular beam epitaxy. Journal De Physique III, 1994, 4, 733-740.	0.3	5
38	Tunable properties of the stable SiSeS Janus monolayer under biaxial strain: First-principles prediction. Optik, 2022, 261, 169123.	2.9	5
39	Si and Ge nanostructures epitaxy on a crystalline insulating LaAlO ₃ (001) substrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 657-662.	1.8	4
40	Experimental molecular adsorption: electronic buffer effect of germanene on Al(1 1 1). 2D Materials, 2019, 6, 035016.	4.4	4
41	Biaxial strain engineering of the electronic and optical properties of Ge2SeS monolayer: Promising for optoelectronic applications. Computational Condensed Matter, 2022, 32, e00717.	2.1	4
42	Electron cyclotron resonance plasma ion beam effects on the formation of SiC on Si(001) characterized by in-situ photoemission. Thin Solid Films, 1994, 241, 305-309.	1.8	3
43	Ge epitaxial island growth on a graphitized C-rich 4H-SiC(0001) surface. Journal of Crystal Growth, 2005, 275, e2275-e2280.	1.5	3
44	Investigation of aluminum phthalocyanine chloride as acceptor material in planar organic solar cells: comparative study with fullerene. Journal of Materials Science: Materials in Electronics, 2021, 32, 27710.	2.2	3
45	Strain enhanced electronic and optical properties in Janus monolayers AsMC3 (M: Sb, Bi). Physica B: Condensed Matter, 2022, 642, 414143.	2.7	3
46	Growth of Fe nanocrystals on LaAlO3 (001) and epitaxial relationship determination by RHEED and XPS. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1393-1396.	0.8	2
47	Performance evaluation and experimental validation of different empirical models for predicting photovoltaic output power. International Journal of Ambient Energy, 2022, 43, 7437-7453.	2.5	2
48	First-principles investigations of structural, electronic and thermoelectric properties of \hat{l}^2 -Sb/Gel2 van der Waals heterostructures. Journal of Computational Electronics, 2022, 21, 582-589.	2.5	2
49	Reply to the comment on "Search for carbon nitride CNx compounds with a high nitrogen content by electron cyclotron resonance plasma depositionâ€, Diamond relat. mater., 3 (1994) 264–269. Diamond and Related Materials, 1994, 3, 1279.	3.9	1
50	Chemical and structural transformations of silicon submitted to H2 or H2/CH4 microwave plasmas. Diamond and Related Materials, 2008, 17, 428-434.	3.9	1
51	Epitaxial growth of Fe islands on LaAlO3 (001) substrates. Journal of Crystal Growth, 2014, 391, 121-129.	1.5	0
52	Synthesis, Structural and Optical Characteristics of Vanadium Doped Cerium Dioxide Layers. SSRN Electronic Journal, 0, , .	0.4	0